

UNIT-3rd Digital Logic Gate Characteristics

Basic Needs

Semiconductor devices :- 2 types $\begin{cases} \text{Bipolar} \rightarrow \\ \text{Unipolar} \end{cases}$

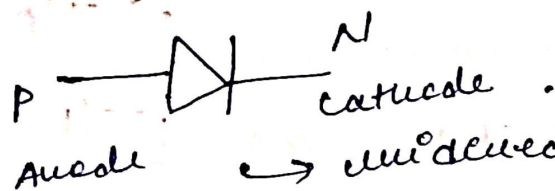
Bipolar $\rightarrow$ Both types of charge carrier

Electrons & Holes

Unipolar $\rightarrow$ Only one type of charge carrier :-
i.e. flow the current.

we use here switching property of this :-

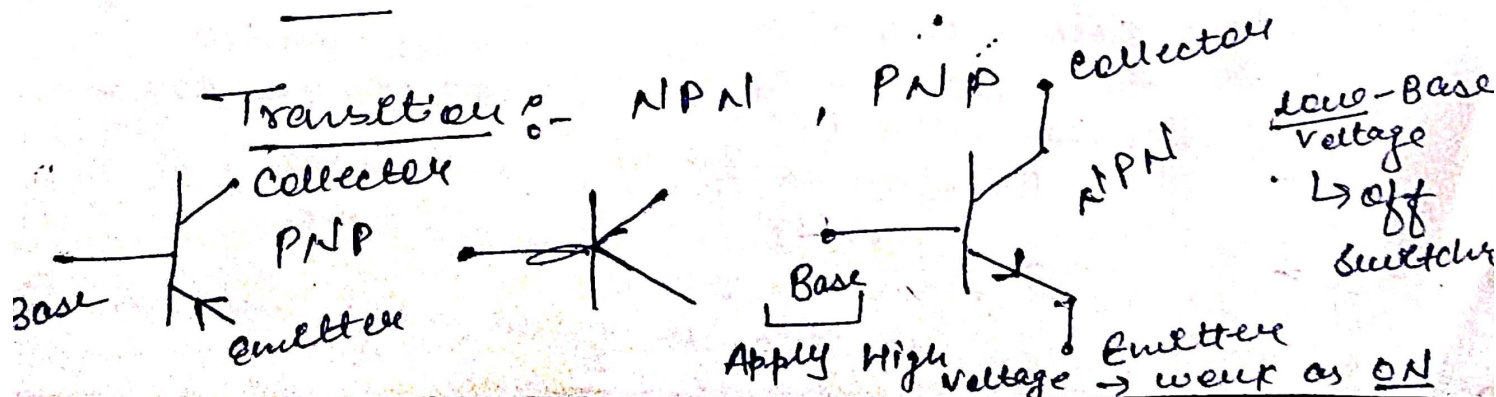
Diode $\rightarrow$ PN Junction Diode



Anode $\rightarrow$ unidirectional property follows

F.B $\rightarrow$ P $\rightarrow$ Anode $\rightarrow$ +ve Terminal of Battery
 $\rightarrow$ N $\rightarrow$ Cathode $\rightarrow$ -ve Terminal of Battery
 $\rightarrow$ So it works as ON Switch

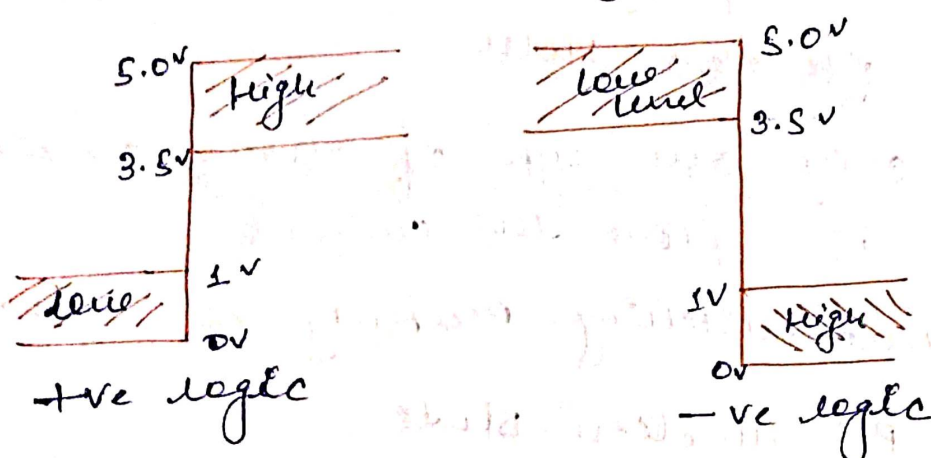
R.B $\rightarrow$ OFF Switch.



Logic Family :- A group of compatible ICs with same logic level and supply voltage fabricated for performing various logic functions referred as a logic family. $\rightarrow$ OR, NOT, AND, etc.

IC $\rightarrow$ Integrated circuit $\rightarrow$ chip

1000 of Transistors fabricated of that chip.



These level are different for different logic family.

(Complementary Metal Oxide Semiconductor Field effect Transistor)

Digital IC

$\rightarrow$ I/P $\rightarrow$ logic OP CMOS
 $\rightarrow$ O/P $\rightarrow$ Bipolar

Bipolar logic family

$\rightarrow$ (use both electrons & holes as a charge carriers)

$\rightarrow$ register, Transistor, Diode are mainly used in Bipolar logic family.

unipolar logic family

$\rightarrow$ (use only one type of charge carriers i.e. Holes or e^-)

$\rightarrow$ MOS devices

- 1) PMOS - P-channel MOSFET
- 2) NMOS - N-channel MOSFET
- 3) CMOS - C-channel MOSFET

Saturated $\rightarrow$ IIL, HTL, RTL, DTL, DCTL, TTL

Non-saturated $\rightarrow$ ECL

$\rightarrow$ only work in Active or cut-off Region

Characteristics of Digital ICs :-

- 1) Propagation Delay, Speed
- 2) Power Dissipation
- 3) Figure of Merit
- 4) Fan-out, Fan-in
- 5) Noise Immunity, Noise Margin
- 6) Operating Temp.
- 7) Current and Voltage Parameters.
- 8) Breadth, Logic Swing

Propagation Delay :-

* Propagation delay is always measured by nano seconds, $\rightarrow 10^{-9}$ of a second

If TTL IC :- $t_{PHL} = 7ns$

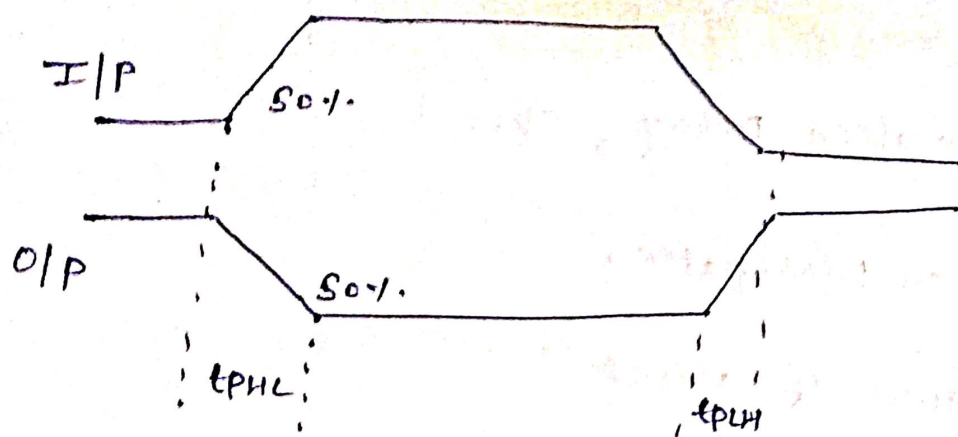
$$t_{PLH} = 11ns$$

Avg Prop Delay = ?

$$= \frac{11+7}{2} = 9ns$$

→ Speed of operations is specified in terms of Propagation delay.

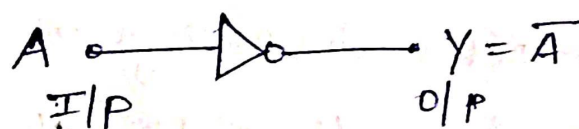
→ Delay time is measured b/w 50% of IP & O/P Transition.



Avg. Propagation Delay = $\frac{t_{PHL} + t_{PLH}}{2}$

t_{PHL} :- Delay time when O/P goes from High to Low

t_{PLH} :- Delay time when O/P goes from Low to High



→ Take some time → i.e → Delay

Power Dissipation :-

→ This is the amount of Power dissipation is an IC in the form of Heat.

→ Excessive temp. could damage the IC, so power dissipation should be $\leq$

→ P.D is determined by the current I_{CC} that is drawn from V_{CC}

$P.D = I_{CC} \times V_{CC}$

5.

Figure of Merit :-

It is always define as a Product of Speed + Power.

$$\text{Figure of Merit} = \text{Propagation delay} \times \text{Power}$$

$$\rightarrow \text{ns} \times \text{mw}$$

$$\rightarrow 10^{-9} \text{ sec} \times 10^{-3} \text{ W}$$

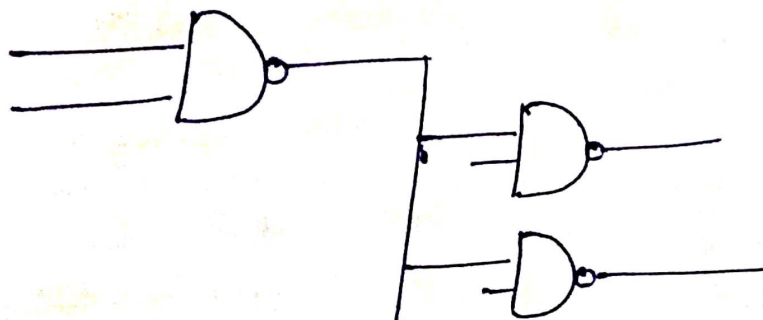
$$\rightarrow 10^{-12} \text{ Joules or Picoseconds}$$

$$\Rightarrow 10^{-12} \text{ PS}$$

Fan-Out :-

No. of Similar gates which can be driven by a Gate.

→ Higher the fan-out, higher the current supplying capacity of a gate.



To other I/Os

Voltage Parameters :-

I_{IL}, I_{OL}	Current Flow	low level I/P	Voltage
V_{IL}, V_{OL}		high level I/P	
		low level O/P	
		high level O/P	

Noise Margin :- It is the limit of Noise Margin that can be present without disturbing proper operation of the circuit.

The circuit ability to tolerate Noise signal is referred to Noise immunity.

Operating Temp. :- at which Temp IC's operates.

0 to 70°C → Commercial Purpose

-55°C to 125°C → Military Application

RTL

70

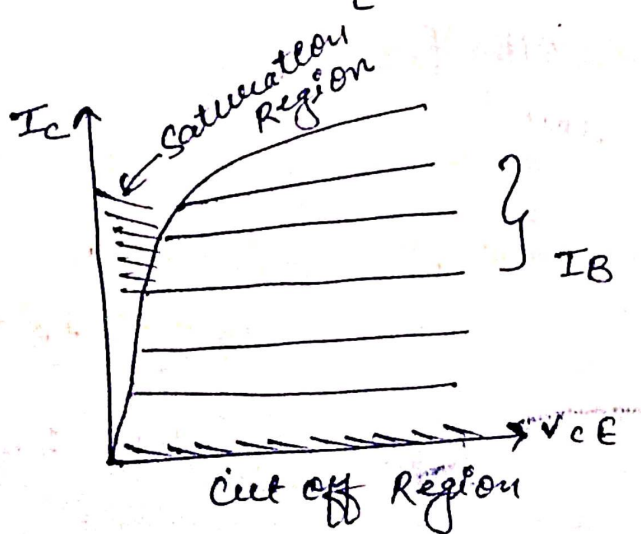
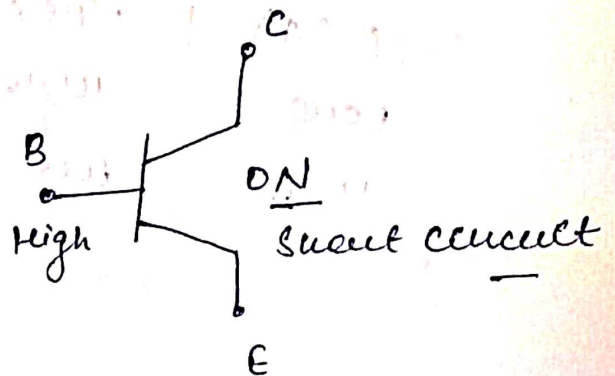
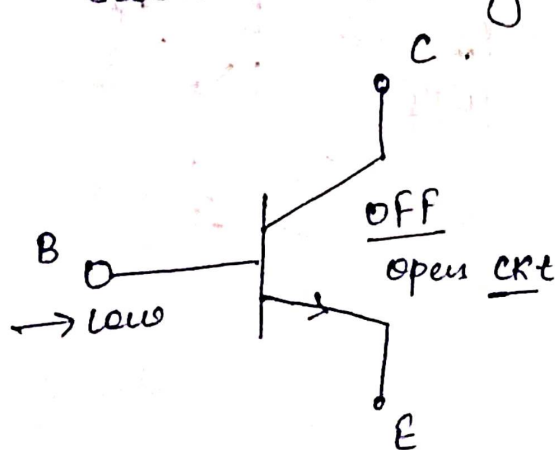
Register Transistor logic

In this we use Register & Transistor to design RTL logic OR we use here NOR gate.
↳ universal gate

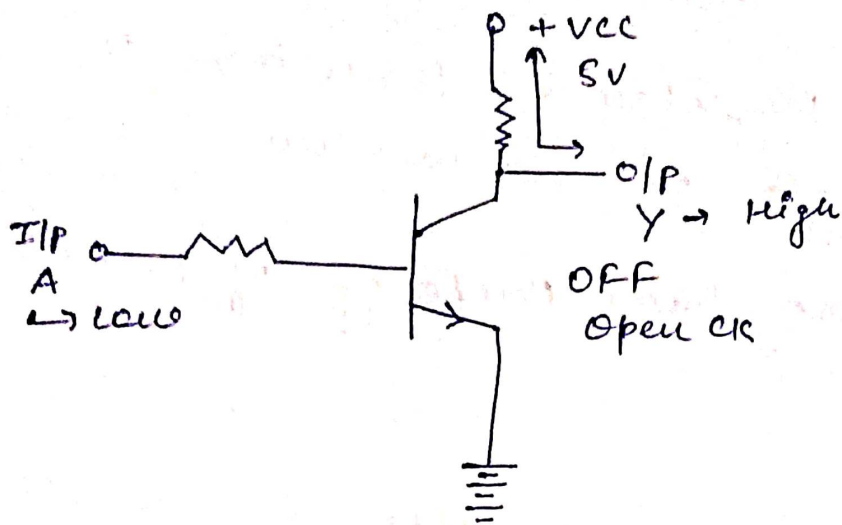
In this we use basic property of transistor
i.e. → ON
→ OFF

→ Cut-Off Region → OFF state → open circuit

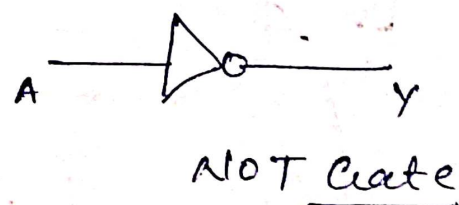
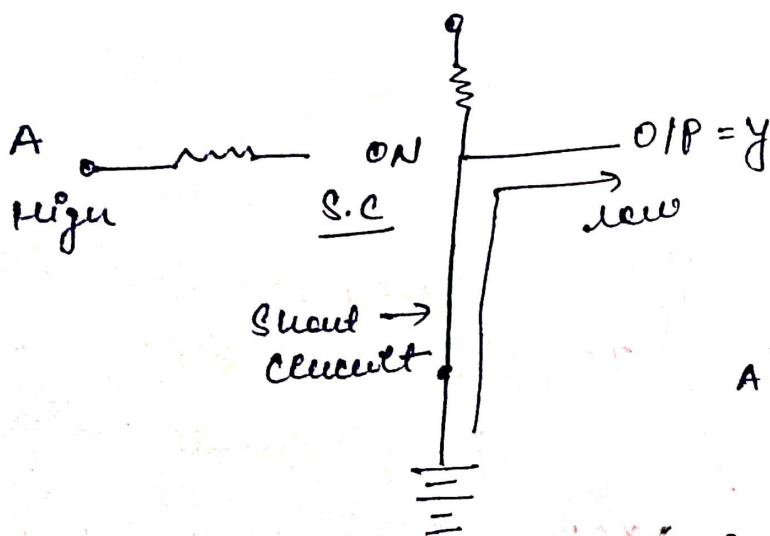
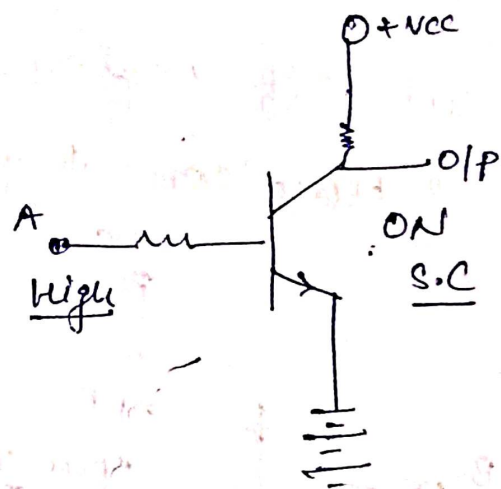
→ Saturation Region → ON state - S.C



8.



$I/P (A)$	$O/P (Y)$
low	High
High	low



RTL Inverter Logic

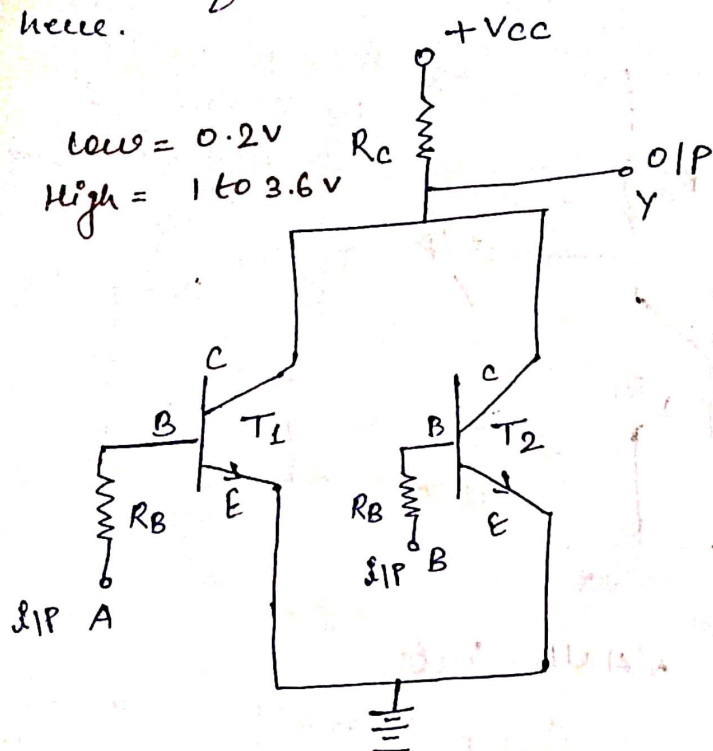
Register Transistor logic

9.

we use here
a no. of I/P
here.

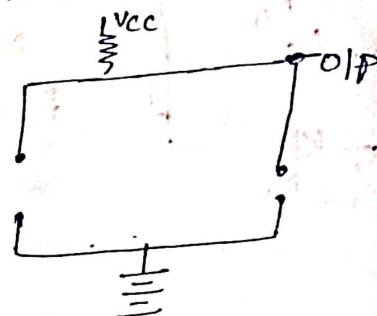
Basic gate - NOR

→ Base is connected
to I/P
→ collector is connect
with V_{CC}

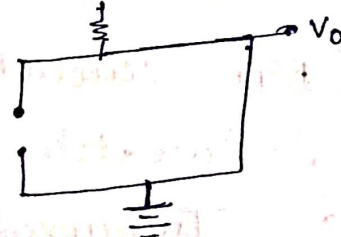


low = 0.2V
High = 1 to 3.6V

case - 1



case - 2



A	B	Y
low	low	High
low	High	low
High	low	low
High	High	low

NOR



Diode Transistor logic (DTL)

This is upgrade version of RTL in this
we improve different characteristics of
logic family i.e.

Fan out, Power dissipation,
Noise Margin etc. $\downarrow$ very high
→ low

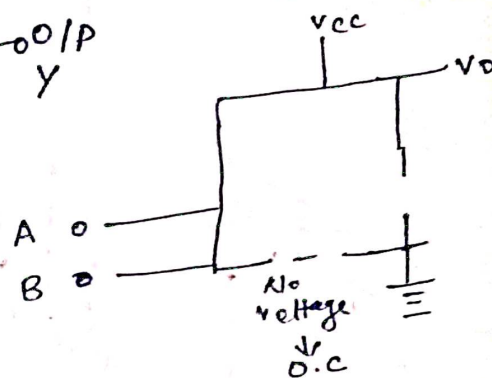
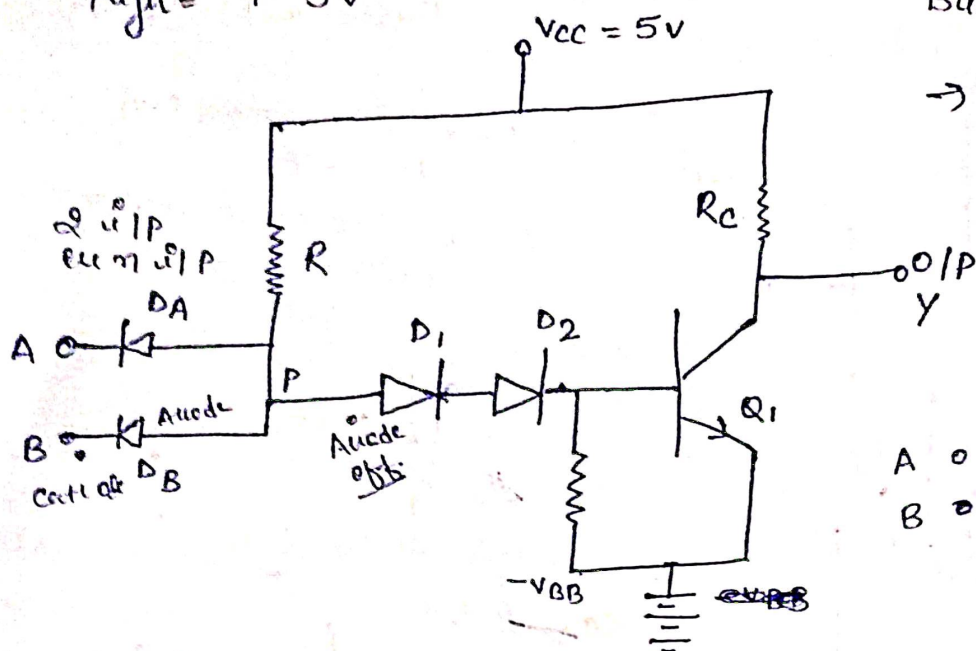
→ we can design NAND
Gate here with
Transistor & Diode.

low = 0.2V
High = 4-5V

10-

Basic Gate $\rightarrow$ NAND

$\rightarrow$ Anode must be connected to higher voltage



$\rightarrow$ DTL circuit naming NAND Gate.

$\rightarrow$ Greater fan out

$\rightarrow$ Improved Noise Margin

* If Transistor base is connected with -ve voltage means cut-off $\rightarrow$ off state $\rightarrow$ O.C

* Diode $\rightarrow$ ON $\rightarrow$ Forward bias $\rightarrow$ current flow $\rightarrow$ S.C
OFF - Reverse bias $\rightarrow$ No current flow $\rightarrow$ O.C

Transistor $\rightarrow$ Base $\rightarrow$ low $\rightarrow$ OFF $\rightarrow$ O.C

Base $\rightarrow$ High $\rightarrow$ ON $\rightarrow$ S.C

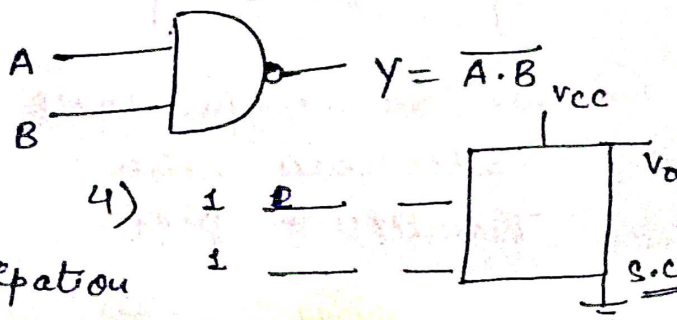
$V_{CE} = \text{saturation}$
low = 0.2V

A	B	Y
0	0	High (1)
0	1	High (1)
1	0	High (1)
1	1	low (0)

complex
Becoz of circuitry

$\rightarrow$ Speed slow, Power Dissipation

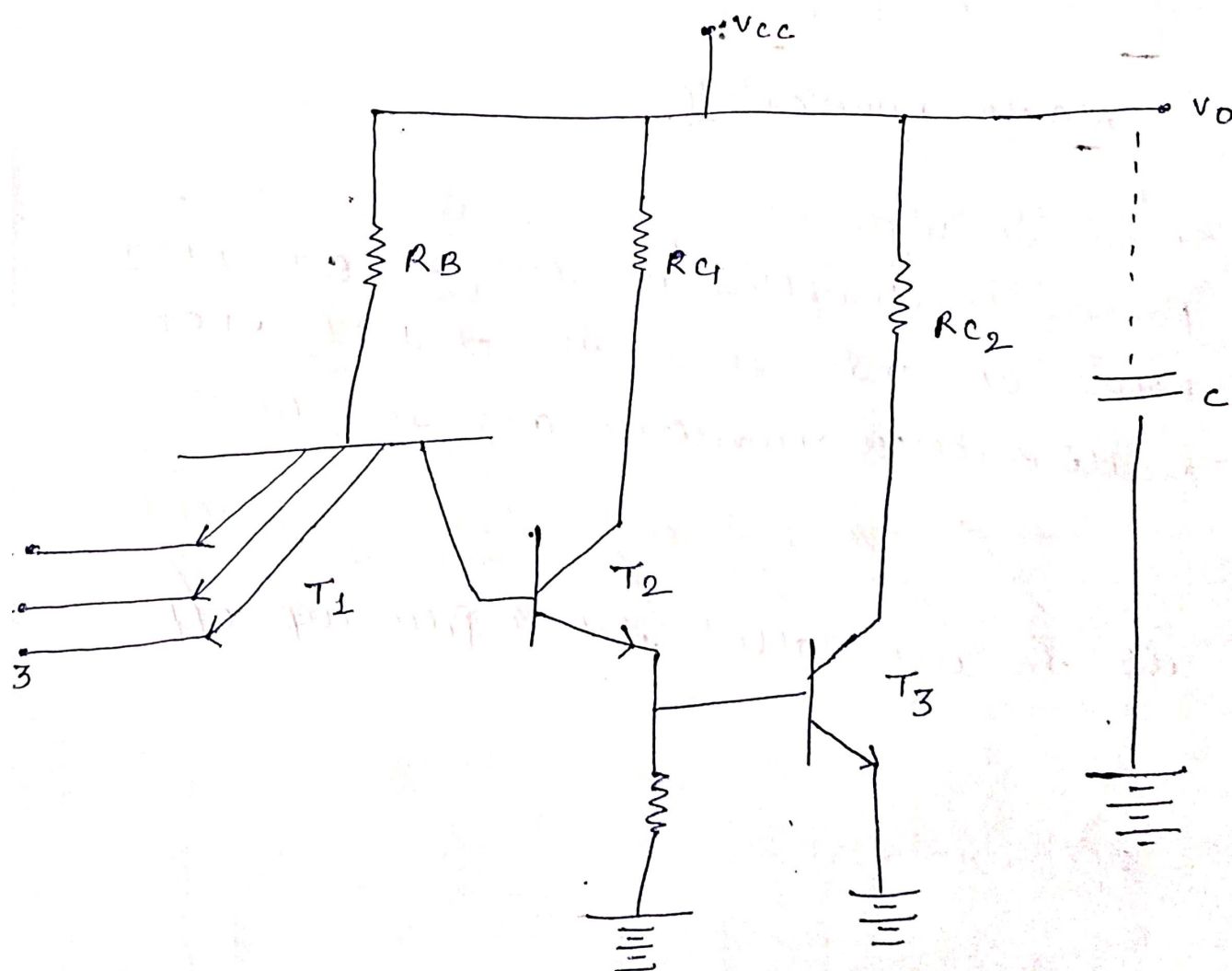
$\rightarrow$ High Fan-out, Noise Margin $\rightarrow$ TTL Next



Transistor Transistor Logic TTL

11.

- This is just modified circuit of DDL.
- Here we are using few i/p is multi-emitter Transistor.
- in this we remove the Diode - D_1 & D_2 with the help of Transistor.



Truth Table :-

A	B	C	V_0
0	0	0	1
0	0	1	1
0	1	0	1
0	1	1	1
1	0	0	1
1	0	1	1
1	1	0	1
1	1	1	0

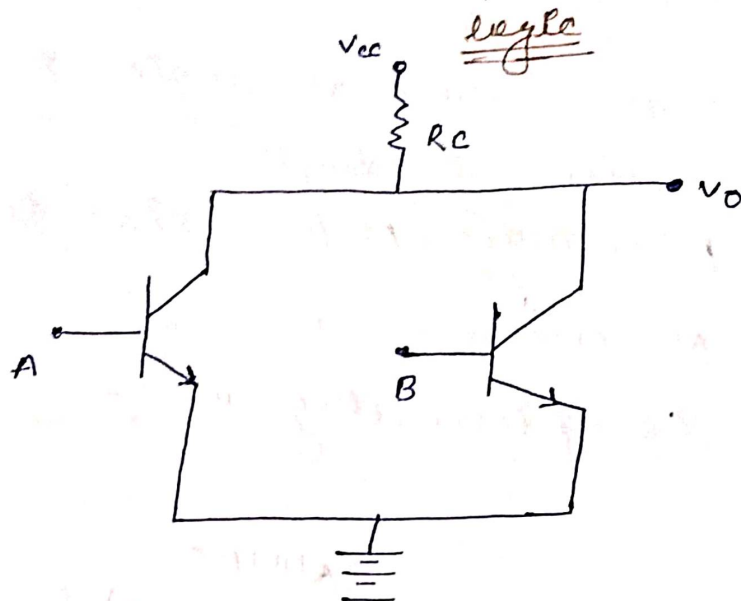
NAND Functionality

- Speed is high
- Power Consumption is less - SSI, MSI
- PMOS, CMOS is used in → LSI, VLSI
- Multi emitter Transistor are use here.

(A T-AND gate output)

13.

Directly coupled Transistor



Basic gate - NOR

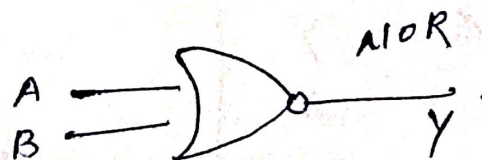
In RTL :-

- Power Noise Margin
- More Power Consumption

- In this I/P directly connected to base of Transistor without using any Register in between Input & Transistor Base
- functionality is similar to RTL, so here we use NOR Gate.

- The I/P of Transistor are low, then transistor in cut-off Region → O.C → ^{Power is going to cut}
- The I/P of Transistor are high, then transistor in saturated Region → S.C

I/P		V _O
A	B	
0	0	1
0	1 → ON	0
1	0	0
1	1	0

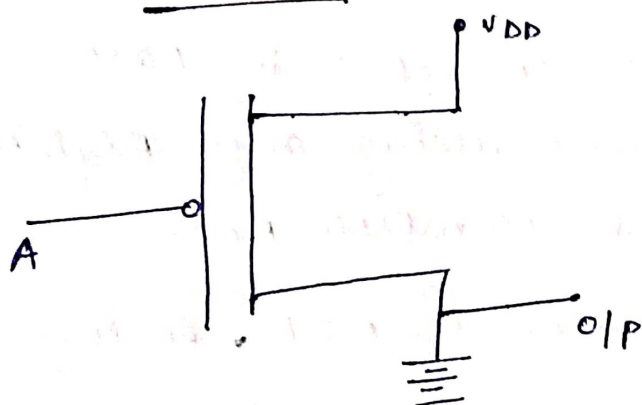


We use here N no. of I/P.
so we make N no. of NOR Gate.

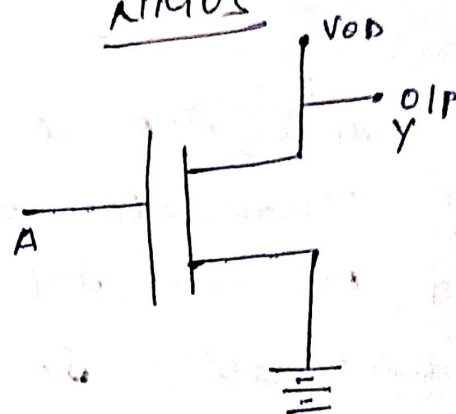
PMOS & NMOS Transistors

- In this we use unipolar logic family.
- current direction is single.
- PMOS → P-channel Metal oxide Semiconductor.
- NMOS → N-channel " " "
- CMOS → Complementary " " "

PMOS



NMOS



Voltage :- PMOS NMOS
0V (0) ON OFF
5V (1) OFF ON

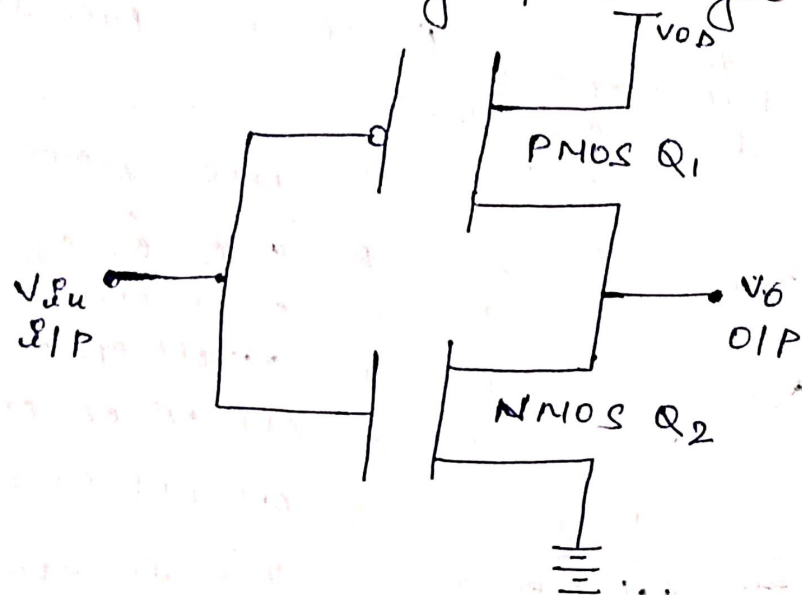
	I/P	O/P
ON	A	Y
OFF	0 → 1	1
OFF	1 → 0	0

	I/P	O/P
ON	A	Y
OFF	0 → 1	1
ON	1 → 0	0

CMOS Inverter

15.

- It is combination of PMOS & NMOS.
- It is very fast logic family.



CMOS or CMOS inverter is same & PMOS & NMOS in these inverter is same.

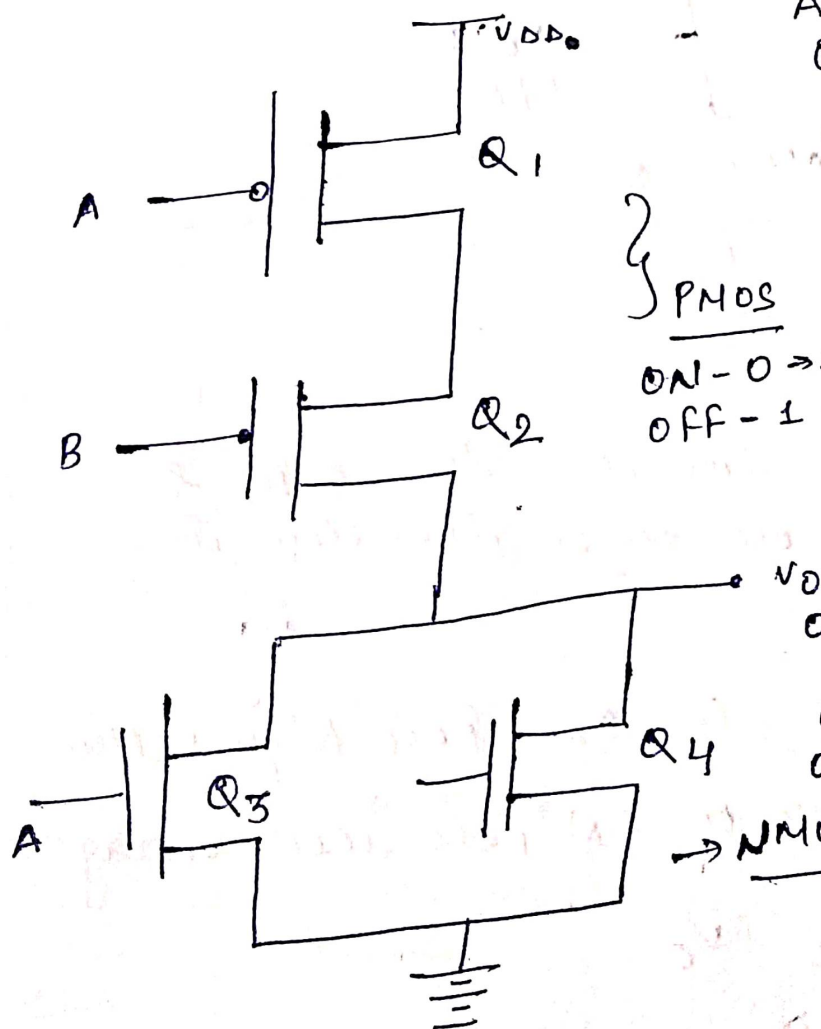
- NMOS is going to ON for high voltage
- PMOS is going to ON for low voltage

V_{IN}	Q_1	Q_2	V_O
0	ON	OFF	1
1	OFF	ON	0

- That's why CMOS also called CMOS Inverter.
- MSI, highest speed logic family as compare to other family.

CMOS NOR Gate

→ CMOS NOR Gate use NMOS & PMOS
↓ ↓
Pull down Pull up
use this functionality
for CMOS NOR Gate



PMOS
ON - 0 → S.C
OFF - 1 → O.C

NMOS
ON - 1 → S.C
OFF - 0 → O.C

PMOS		NMOS		
Q ₁	Q ₂	Q ₃	Q ₄	V _O
ON	ON	OFF	OFF	1
ON	OFF	OFF	ON	0
OFF	ON	ON	OFF	0
OFF	OFF	ON	ON	0

This is work
as NOR Gate
operation.

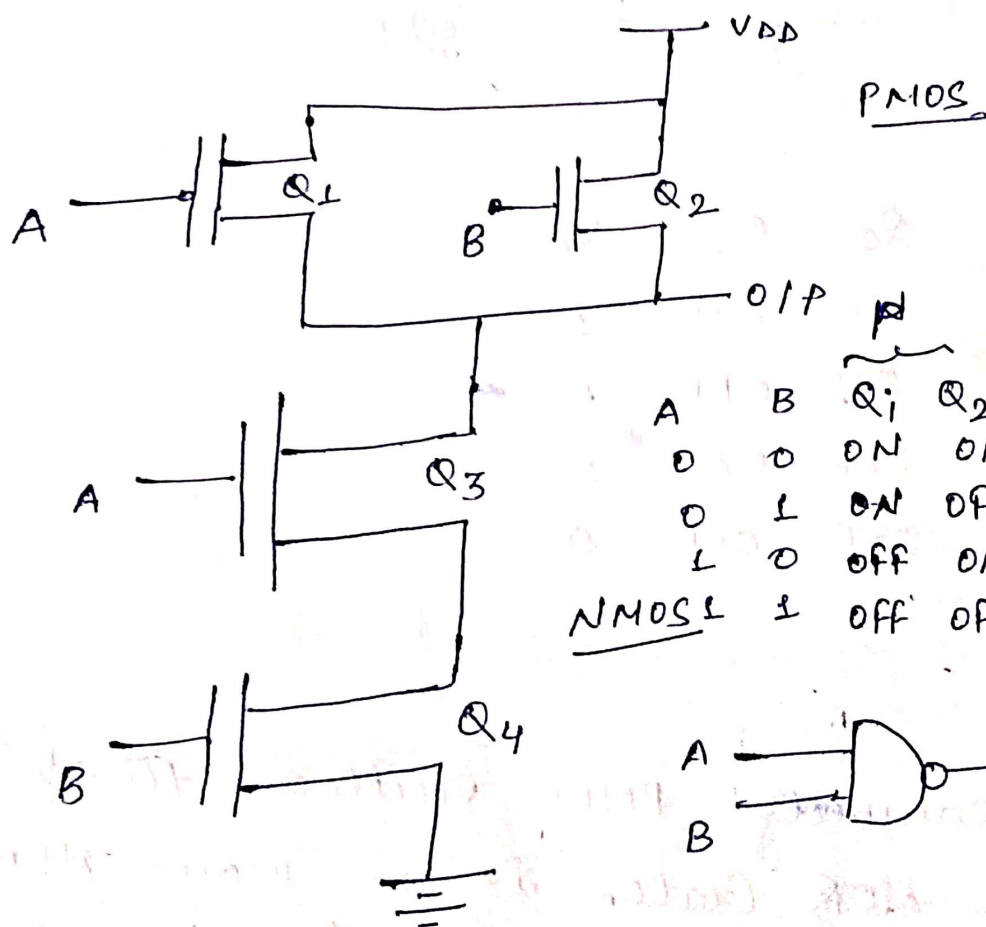
$$A \text{ --- } B \text{ --- } \bigcirc \text{ --- } Y = \overline{A+B}$$

17.

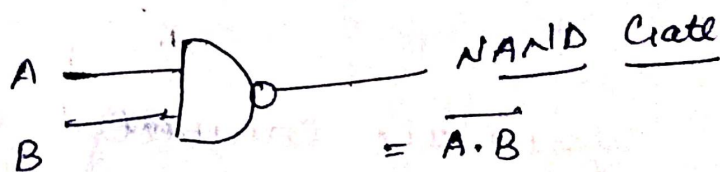
CNOS NAND Gate

→ CNOS NAND Gate are designed by NMOS & PMOS logic family.

→ In this NMOS is pull up mode & PMOS is pull down mode, only.

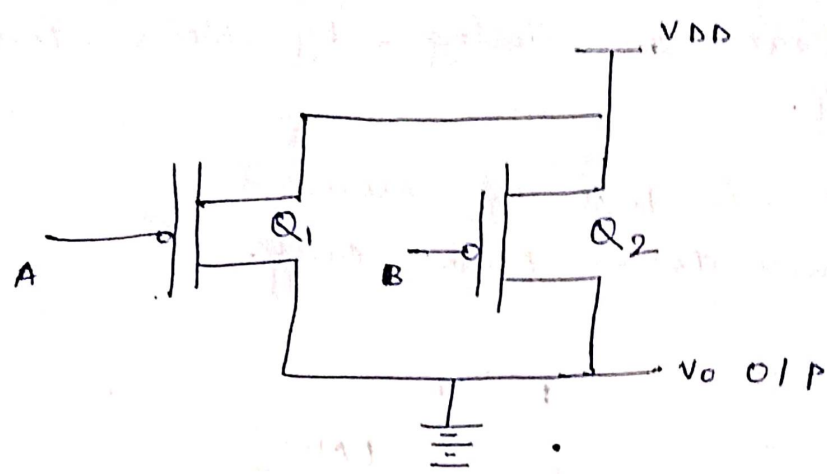


		<u>PMOS</u>		<u>NMOS</u>		
		Q ₁	Q ₂	Q ₃	Q ₄	V _O
A	B	ON	ON	OFF	OFF	1
0	0	ON	OFF	OFF	ON	1
0	1	OFF	ON	ON	OFF	1
1	0	OFF	OFF	ON	ON	0



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PMOS NAND Gate

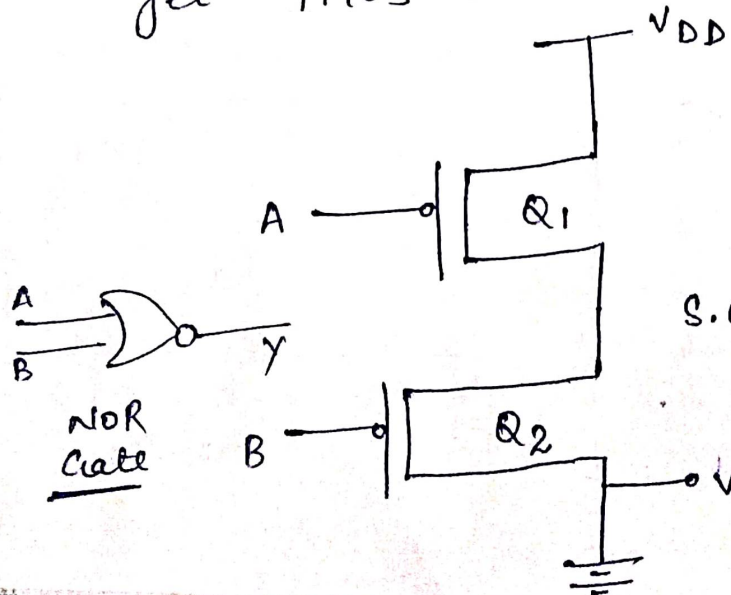


O - ON - S.C
OFF → 1 - O.C

A	B	Q ₁	Q ₂	V _O
0	0	ON	ON	1
0	1	ON	OFF	1
1	0	OFF	ON	1
1	1	OFF	OFF	0

PMOS NOR Gate

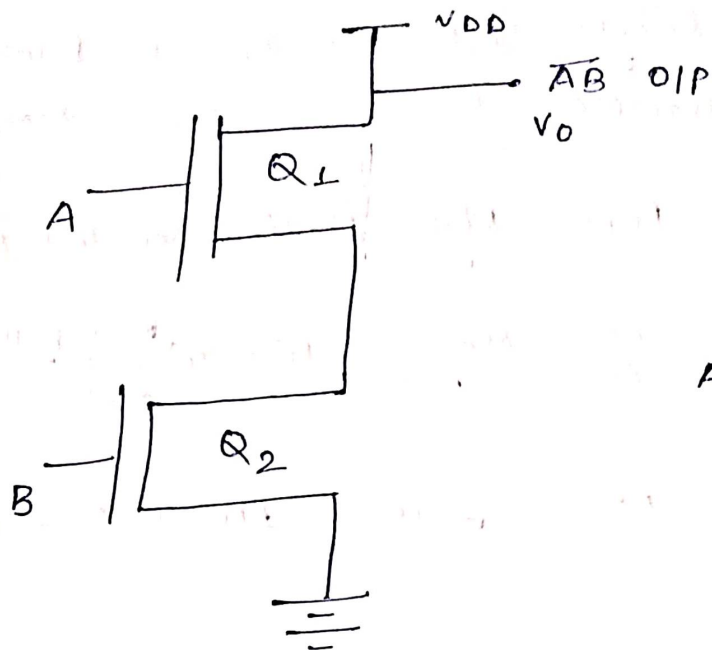
when we connected PMOS vertical then we get PMOS NOR Gate. if we want N no. of O/P then we add no. of P/P here. like vertical.



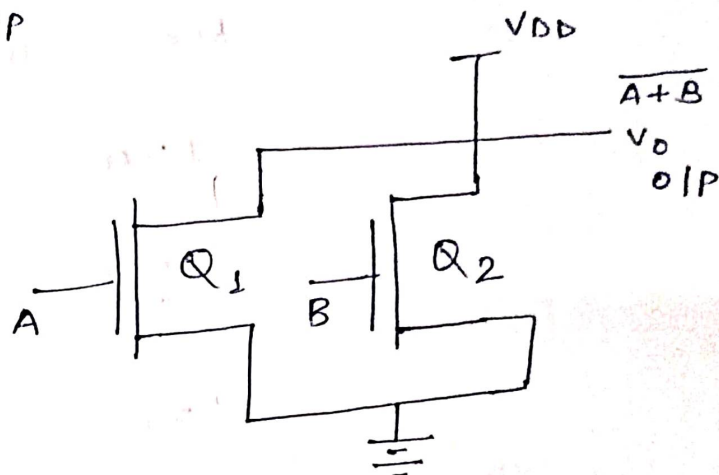
A	B	Q ₁	Q ₂	V _O
0	0	ON	ON	1
0	1	ON	OFF	0
1	0	OFF	ON	0
1	1	OFF	OFF	0

S.C - ON → 0
OFF → 1
O/P ↓
O.C 1

Designing Universal Gates using NMOS



NAND



NOR

A	B	Q ₁	Q ₂	V _O O/P
OFF → 0	0	OFF	OFF	1
↓ O.C	0	OFF	ON	1
1	0	ON	OFF	1
ON → 1	1	ON	ON	0
↓ S.C				

A	B	Q ₁	Q ₂	V _O O/P
0	0	OFF	OFF	1
0	1	OFF	ON	0
1	0	ON	OFF	0
1	1	ON	ON	0
		↓ S.C		

Comparison of logic family 20.

	RTL	DCTL	DTL	TTL	ECL	IL ²	CMOS
Parameter & Components	Register & Transistor Power	Register & Transistor	R, D, T	R, T	R, T	T	PMOS NMOS
Noise - Margin	Poor	Poor	high	Medium	low	high	high
Fan - out	low (4)	low (4)	Medium (8)	high (10)	very high (15)	8-11	50
Power - dissipation (mw)	30	10	8-12	10	40-55	5-25	1
Delay (ns)	12	10	30	10	2 (10k)	25-250	7
Figure of Merits	144	1800	300	100	100	40 [100k]	4 0.7

CMOS $\rightarrow$ is low power consumption.

ECL is fastest logic family